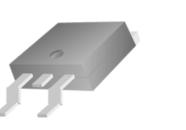
Analog Power AM60N02-10D

## N-Channel 20-V (D-S) MOSFET

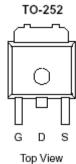
These miniature surface mount MOSFETs utilize a high cell density trench process to provide low  $r_{DS(on)}$  and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

V <sub>DS</sub> (V)	$r_{DS(on)} m(\Omega)$	<b>I</b> <sub>D</sub> (A)
20	$10 @ V_{GS} = 4.5V$	58
20	$16 @ V_{GS} = 2.5V$	46

- Low r<sub>DS(on)</sub> provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe DPAK saves board space
- Fast switching speed
- High performance trench technology



PRODUCT SUMMARY



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25 °C UNLESS OTHERWISE NOTED)				
Parameter		Symbol	Limit	Units
Drain-Source Voltage		$V_{DS}$	20	V
Gate-Source Voltage			±8	V
Continuous Drain Current <sup>a</sup>	$T_C=25^{\circ}C$	$I_D$	58	Α
Pulsed Drain Current <sup>b</sup>		$I_{DM}$	40	A
Continuous Source Current (Diode Conduction) <sup>a</sup>		$I_S$	30	A
Power Dissipation <sup>a</sup>	$T_C=25^{\circ}C$	$P_{\mathrm{D}}$	50	W
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to 175	°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Maximum	Units	
Maximum Junction-to-Ambient <sup>a</sup>	$R_{ heta JA}$	50	°C/W	
Maximum Junction-to-Case	$R_{ heta JC}$	3.0	°C/W	

1

## Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Analog Power AM60N02-10D

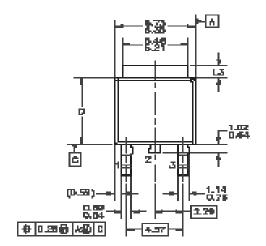
Parameter	Symbol	Total Constitution	Limits			TI*4	
Farameter	Symbol Test Conditions		Min	Тур	Max	Unit	
Static							
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \text{ uA}$	0.4			V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \ V, \ V_{GS} = 8 \ V$			±100	nA	
Zara Cata Valtaga Drain Current	IDSS	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}$			1	uA	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 16 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			25	uA	
On-State Drain Current <sup>A</sup>	ID(on)	$V_{DS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	34			Α	
Did o Di A		$V_{GS} = 4.5 \text{ V}, I_{D} = 51 \text{ A}$			10	mQ.	
Drain-Source On-Resistance <sup>A</sup>	fDS(on)	$V_{GS} = 2.5 \text{ V}, I_{D} = 41 \text{ A}$			16	ms2	
Forward Tranconductance <sup>A</sup>	gs	$V_{DS} = 10 \text{ V}, I_D = 51 \text{ A}$		22		S	
Diode Forward Voltage	$V_{\mathrm{SD}}$	$I_S = 34 \text{ A}, V_{GS} = 0 \text{ V}$		1.1		V	
Dynamic <sup>b</sup>							
Total Gate Charge	Qg	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V},$ $I_D = 51 \text{ A}$		4.0			
Gate-Source Charge	Qgs			1.1		nC	
Gate-Drain Charge	Qgd			1.4			
Turn-On Delay Time	t <sub>d(on)</sub>			16			
Rise Time	$t_{\rm r}$	$V_{\rm DD}$ = 15 V, $R_{\rm L}$ = 25 $\Omega$ , $I_{\rm D}$ = 34 A,		5		nS	
Turn-Off Delay Time td(off)		$V_{GEN} = 10 V$		23		113	
Fall-Time	$t_{\mathrm{f}}$			3			

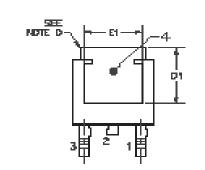
## Notes

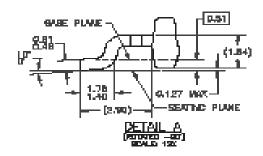
- a. Pulse test:  $PW \le 300us duty cycle \le 2\%$ .
- b. Guaranteed by design, not subject to production testing.

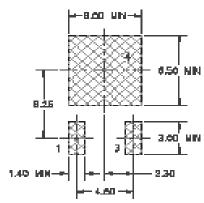
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## Package Information

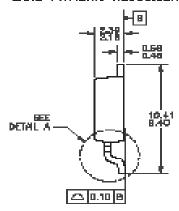








LAND PATTERN RECOMMENDATION



NOTES: UNLESS OTHERWISE SPECIFIED

- ALL DIPERSONS ARE IN ILLIMETERS.
  THIS PERSONCE CONFORMS TO JEDEC, TO-262,
  168ME C, VARIATION AA IN AB, DATED NOW 1989.
  DIMENSIONING AND TOLERANCING PER
- ASNE 714-04-1894.
  HEAT SINK TOP EDGE COLLD BE IN CHANFERED CORRERS OR EDGE PROTEURION.
  DIMENSIONS 13,0,61-601 TABLE:

	OPTION JA	47101 40
	0.0 -1.27	1.62-7.00
		B.445—B.460
	4.42	310 H H
100		